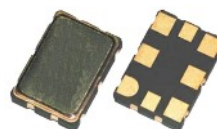


FEATURES

- EG_JF Series oscillators, Ultra-low Jitter
- Outputs CMOS, LVPECL, LVDS, CML Differential outputs: 15~2100MHz
- HCSL Differential Outputs: 15~700MHz
- RMS phase jitter 150fs typical
- ITAR Free


GENERAL SPECIFICATIONS

Model	EGTJF	EGPJF	EGDJF	EGQJF	EGCJF
Output Logic Type	CMOS	LVPECL	LVDS	CML	HCSL
Frequency Range	15 ~250MHz	15 ~ 2100MHz	15 ~ 2100MHz	15 ~ 2100MHz	15 ~ 700MHz
Load	15pF max	50Ω into V _{DD} -2V or Thevenin equivalent	100Ω between OUT and OUT-1	50Ω to V _{DD}	50Ω to GND
Power Supply Voltage (V_{DD})	+1.8V±5% or +2.5V±10% or +3.3V±10%	+2.5V±10% or +3.3V±10%	+1.8V±5% +2.5V±10% +3.3V±10%	+1.8V±5% +2.5V±10% +3.3V±10%	+1.8V±5% or +2.5V±10% or +3.3V±10%
Output 'HIGH' Voltage	V _{DD} -0.4V min	V _{DD} -1.165V min. V _{DD} -0.8V max.	V _{DD} : 1.4V typical V _{DD} : 1.6V max.	V _{DD} : -0.085V min. V _{DD} : = max.	V _{DD} : 0.66V min. V _{DD} : 1.15V max.
Output 'LOW' Voltage	V _{DD} x 0.1 max 0.2V max for 1.8V	V _{DD} : -2.0V min.	V _{DD} : 1.1V typical	V _{DD} : -0.6V min.	V _{DD} : 0.0V min.
Duty Cycle	50%±5% 50%±10% 1.8V only	50%±5%	50%±5%	50%±5%	50%±5%
Rise Time (Tr) Fall Time (Tf) (20% ~ 80% waveform)	5.0ns max.	0.4ns max.	0.4ns max.	0.4ns max.	0.4ns max.
Current Cons. 50MHz: at V _{DD} = 3.3V 250MHz:	70mA typical 80mA typical	100mA typical 120mA max.	75mA typical 90mA max.	70mA typical 85mA max.	80mA typical 100mA max.
Current with output Disabled	63mA typical	99mA typical	74mA typical	69mA typical	79mA typical
RMS Phase Jitter (Typical) 12kHz to 20MHz	156.250MHz: 159fs ; 491.520MHz : 155fs ; 644.530 MHz : 151fs ; 2000MHz : 163fs				
Output Voltage Swing	-----	595mV(min) 930mV (max)	250mV (min) 450mV (max)	200mV (min) 600mV (max)	620mV (min) 780mV (max)
Storage Temp	-55C +150C max limits				
Ageing at Ta = 25°C	±3ppm max. first year; 2±ppm max. per year thereafter				
V Cont Centre	+0.9V for V _{DD} = +1.8V	+1.25V for V _{DD} = +2.5V		+1.65V for V _{DD} = +3.3V	
V Cont Range	+0.0V ~ +1.8V	+0.25 ~ +2.25V		+0.3V ~ +3.0V	
Freq Pulling Range	±100ppm min. ±200ppm available	±100ppm min. ±200ppm available		±100ppm min. ±200ppm available	
Linearity	±1% typical ; ±10% max				
V Cont I/P Impedance	5 MΩ (min)				
Bandwidth	10kHz typ. Measure at -3dB				

Frequency Stability Codes	Frequency stability over operating temp. Range	±25ppm	±50ppm	±100ppm	If non-standard please enter the desired stability after the 'C' or 'I' Example: 'C20' is ±20ppm over -10° to +70°C.
	Commercial -10° to +70°C	A	B	C	
	Industrial -40° to 85°C	D	E	F	

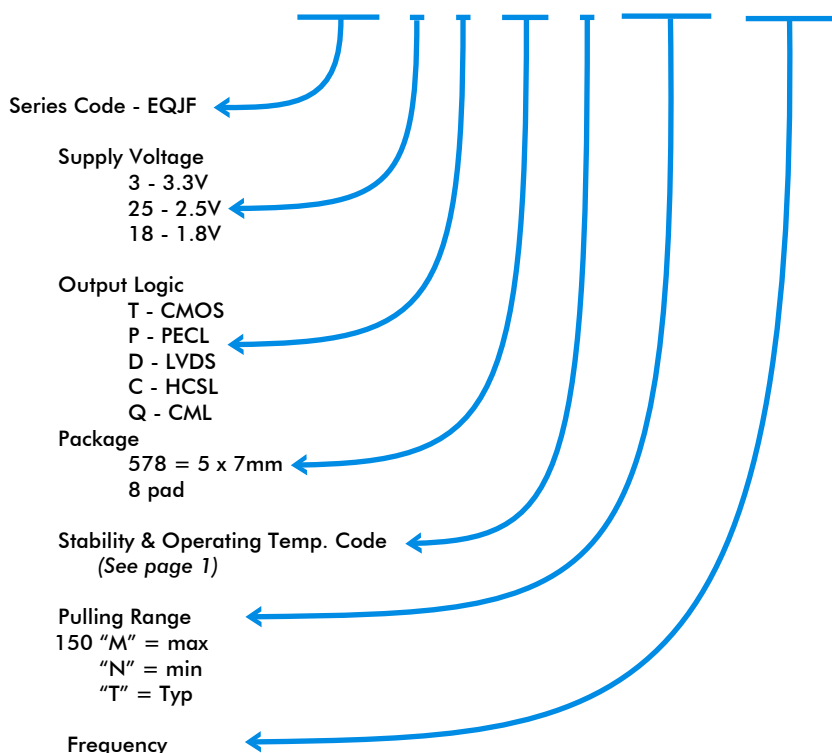
ENVIRONMENTAL PERFORMANCE SPECIFICATION

Green Requirement	ROHS Compliant, pB (lead) free in accordance with EU Directive 2002/95/EC 6/6 (2002/95/EC) and WEEE (2002/96/EC)
Second Level Interconnect	e4
Moisture Sensitivity Level	Level 1 (infinite) according to IPC/JEDEC J-STD-020D.1
Storage Temperature Range	-55° to +150°C
Humidity	85% RH, 85°C, 48 hours
Fine Leak	MIL-STD-883 Method 1014, condition A
Gross Leak	MIL-STD-883 Method 1014, condition C
Solderability	MIL-STD-202F Method 208E
Reflow	260°C for 10 seconds, twice
Vibration	MIL-STD-202F Method 204, 35G, 50 to 2000Hz
Shock	MIL-STD-202F Method 213B, test cond. E, 1000g ½ sine wave
Resistance to Solvent	MIL-STD-202F Method 215
Temperature Cycling	MIL-STD-883 Method 1010
ESD Rating	Human body model (HBM): 2000V min.
Pad Surface Finish	Gold (0.3µm to 1.0µm) over nickel (1.27µm to 8.89µm)
Weight of Device	0.045 gm typical

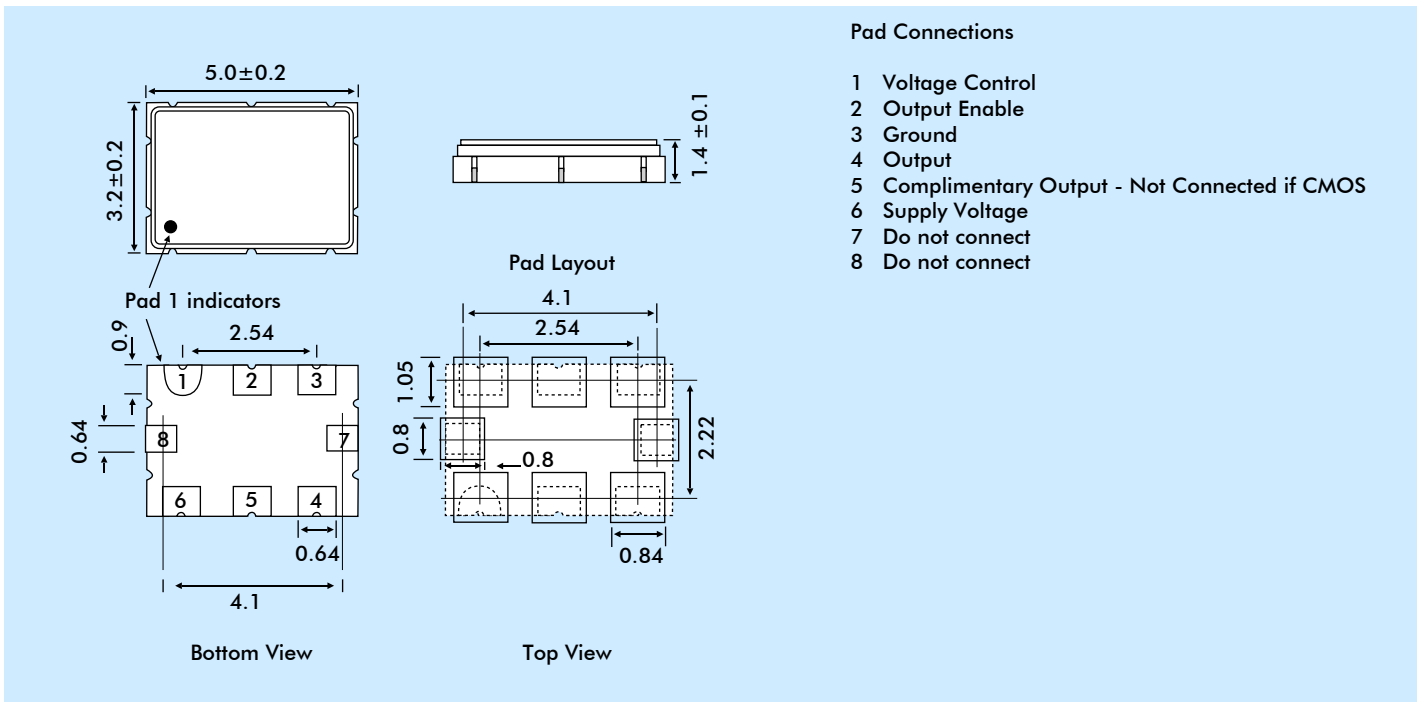
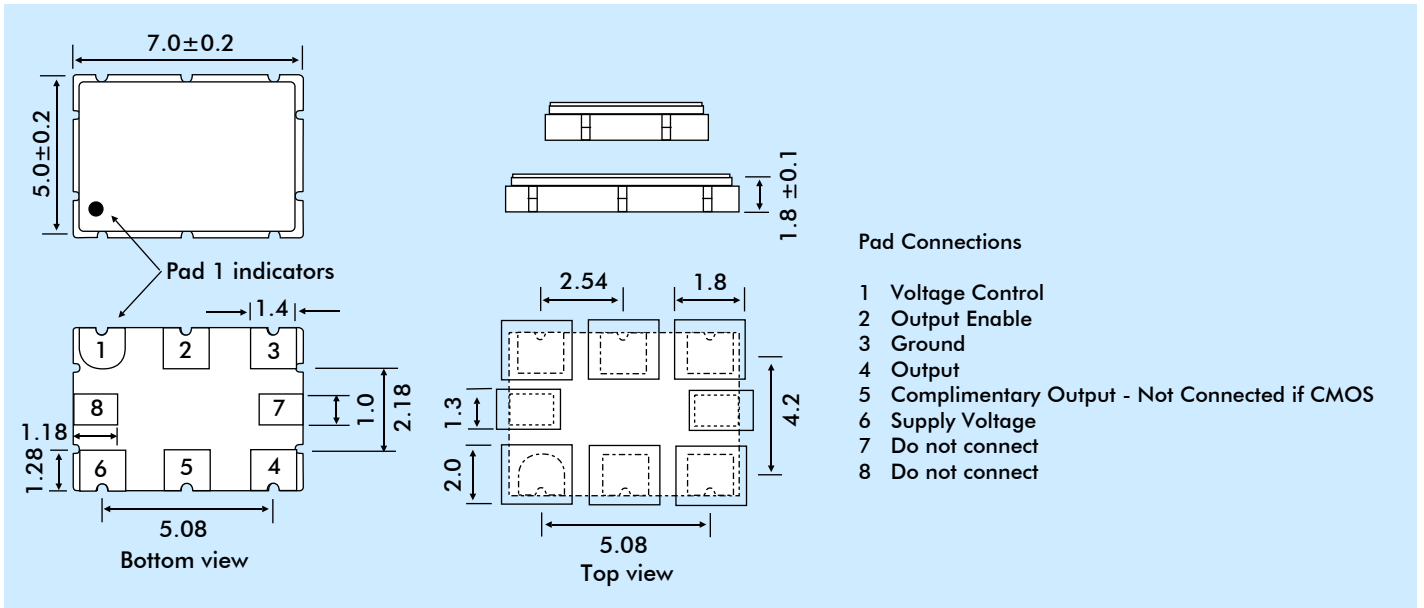
PART NUMBERING

EQJF oscillator part numbers are configured as per the following example: EG_JF-3-P-578-E-150M-250MHz

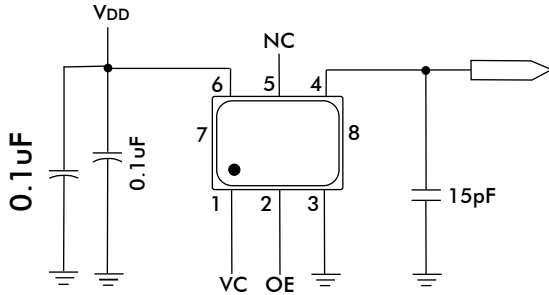
EG_JF - 3 - P - 578 - E - 150M - 250MHz



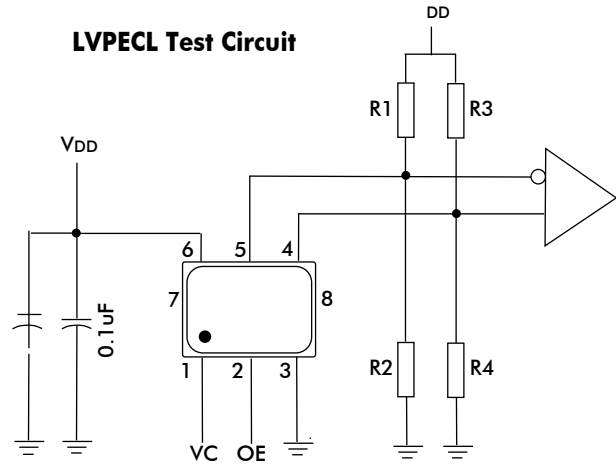
OUTLINE & DIMENSIONS



CMOS Test Circuit

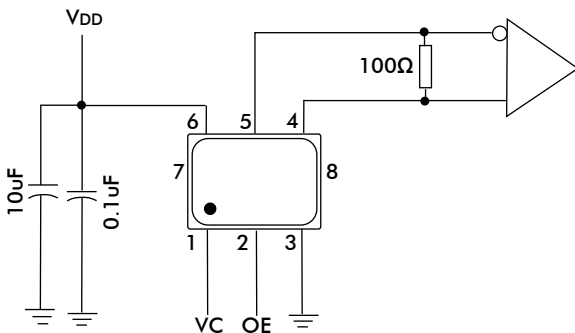


LVPECL Test Circuit

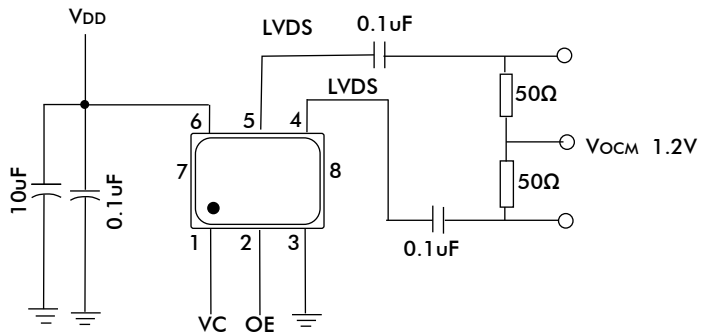


$V_{DD} = 3.3v$; $R1=R3=127\Omega$; $R2-R4=82.5\Omega$
 $V_{DD} = 2.5v$; $R1=R3=250\Omega$; $R2-R4=62.5\Omega$

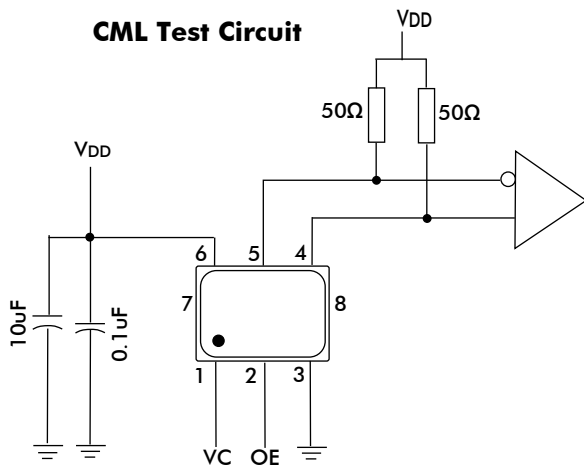
LVDS Test Circuit (3.3V and 2.5V)



LVDS Test Circuit (1.8V only)



CML Test Circuit



HCSL Test Circuit

